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# **NCE25G120P**

## NCE25G120P

## 1200V, 25A, Trench NPT IGBT

#### **Features**

- Trench NPT( Non Punch Through) IGBT
- High speed switching
- Low saturation voltage: V<sub>CE(sat)</sub>=2.0V@I<sub>C</sub>=25A
- High input impedance

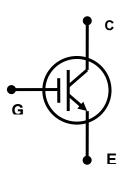


### **Applications**

- Inductive heating, Microwave oven, Inverter, UPS, etc.
- Soft switching applications

### **General Description**

Using advanced Trench NPT technology, NCE's 1200V IGBTs offers superior conduction and switching performances, and easy parallel operation with exceptional avalanche ruggedness. This device is designed for soft switching applications.



## **Absolute Maximum Ratings**

| Symbol              | Description  | Ratings     | Units |
|---------------------|--|-------------|-------|
| V <sub>CES</sub>    | Collector to Emitter Voltage                         | 1200        | V     |
| $V_{GES}$           | Gate to Emitter Voltage                              | +/-30       | V     |
| I <sub>C</sub>      | Continuous Collector Current @T <sub>C</sub> =25°C   | 50          | Α     |
|                     | Continuous Collector Current @T <sub>C</sub> =100°C  | 25          | Α     |
| I <sub>CM</sub> (1) | Pulsed Collector Current                             | 90          | Α     |
| $P_D$               | Maximum Power Dissipation @T <sub>C</sub> =25°C      | 312         | W     |
|                     | Maximum Power Dissipation @T <sub>C</sub> =100°C     | 125         | W     |
| TJ                  | Operating Junction Temperature                       | -55 to +150 | °C    |
| T <sub>stg</sub>    | Storage Temperature Range                            | -55 to +150 | °C    |
|                     | Maximum Lead Temp. for soldering Purposes, 1/8" from |             |       |
| $T_L$               | case for 5seconds                                    | 300         | °C    |

#### Notes:

<sup>1.</sup> Repetitive rating, Pulse width limited by max. junction temperature



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### **Thermal Characteristics**

| Symbol          | Parameter                               | Тур. | Max. | Units |
|-----------------|---|------|------|-------|
| R <sub>JC</sub> | Thermal Resistance, Junction to Case    | -    | 0.4  | °C/W  |
| $R_{JA}$        | Thermal Resistance, Junction to Ambient | -    | 40   | °C/W  |

## Electrical Characteristics of the IGBT $\tau_{c=25^{\circ}\text{C}}$

| Symbol                     | Parameter                              | Test Conditions  | Min.     | Тур.      | Max.     | Units    |
|----------------------------|--|--|----------|-----------|----------|----------|
| Off Characteristics        |  |  |          |           |          |          |
| BV <sub>CES</sub>          | Collector to Emitter Breakdown Voltage | V <sub>GE</sub> =0V, Ic=1mA  | 1200     | -         | -        | V        |
| I <sub>CES</sub>           | Collector Cut-Off Current              | V <sub>CE</sub> =V <sub>CES</sub> , V <sub>GE</sub> =0V            | -        | -         | 1        | mA       |
| I <sub>GES</sub>           | G-E Leakage Current                    | V <sub>GE</sub> =V <sub>GES</sub> , V <sub>CE</sub> =0V            | -        | -         | +/-250   | nA       |
| On Char                    | acteristics                            |  | •        |           |          |          |
| $V_{GE(th)}$               | G-E Threshold Voltage                  | I <sub>C</sub> =25mA, V <sub>CE</sub> =V <sub>GE</sub>             | 4.0      | 5.5       | 7.0      | V        |
|                            | Collector to Emitter Saturation        | I <sub>C</sub> =25A, V <sub>GE</sub> =15V<br>T <sub>C</sub> =25°C  | -        | 2         | 2.5      | V        |
| $V_{CE(sat)}$              | Voltage                                | I <sub>C</sub> =25A, V <sub>GE</sub> =15V<br>T <sub>C</sub> =125°C | -        | 2.15      | -        | V        |
| Dynamic                    | : Characteristics                      |  |          |           |          |          |
| C <sub>ies</sub>           | Input Capacitance                      |  | -        | 3700      | -        | pF       |
| $C_oes$                    | Output Capacitance                     | $V_{CE}$ =30V, $V_{GE}$ =0V,                                       | -        | 130       | -        | pF       |
| $C_res$                    | Reverse Transfer                       | f=1MHz   | -        | 80        | -        | pF       |
| Constants in               | Capacitance                            |  |          |           |          |          |
|                            | g Characteristics                      |  | 1        | 50        | <u> </u> |          |
| t <sub>d(on)</sub>         | Turn-On Delay Time Rise Time           |  | -        | 50        | -        | ns       |
| t <sub>r</sub>             |  | $V_{CC}$ =600V, $I_{C}$ =25A,                                      | -        | 60<br>190 | 90       | ns       |
| $\frac{t_{d(off)}}{t_{f}}$ | Turn-Off Delay Time Fall Time          | $R_G$ =10 $\Omega$ , $V_{GE}$ =15 $V$ ,                            |          | 100       | 180      | ns       |
| Ε <sub>on</sub>            | Turn-On Switching Loss                 | Resistive Load,  | -        | 4.1       | 6.2      | ns<br>mJ |
| E <sub>off</sub>           | Turn-Off Switching Loss                | T <sub>C</sub> =25°C   |          | 0.96      | 1.5      | mJ       |
| E <sub>ts</sub>            | Total Switching Loss                   |  | <u> </u> | 5.06      | 7.7      | mJ       |
|                            | Turn-On Delay Time                     |  | _        | 50        | -        | ns       |
| $\frac{t_{d(on)}}{t_r}$    | Rise Time                              |  |          | 60        | _        | ns       |
| t <sub>d(off)</sub>        | Turn-Off Delay Time                    | $V_{CC}$ =600V, $I_{C}$ =25A,                                      | _        | 200       | _        | ns       |
| <u><b>t</b>α(οπ)</u>       | Fall Time                              | $R_G$ =10 $\Omega$ , $V_{GE}$ =15 $V$ ,<br>Resistive Load,         | _        | 154       | _        | ns       |
| E <sub>on</sub>            | Turn-On Switching Loss                 |  | _        | 4.3       | 6.9      | mJ       |
| E <sub>off</sub>           | Turn-Off Switching Loss                | T <sub>C</sub> =125°C  | _        | 1.5       | 2.4      | mJ       |
| E <sub>ts</sub>            | Total Switching Loss                   |  | _        | 5.8       | 9.3      | mJ       |
| Q <sub>g</sub>             | Total Gate Charge                      |  | _        | 200       | 300      | nC       |
| $Q_{ge}$                   | Gate to Emitter Charge                 | $V_{CC}$ =600 $V$ , $I_{C}$ =25 $A$ ,                              | _        | 15        | 23       | nC       |
| Q <sub>gc</sub>            | Gate to Collector Charge               | V <sub>GE</sub> =15V   | -        | 100       | 150      | nC       |



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### **Typical Performance Characteristics**

**Figure 1. Typical Output Characteristics** 

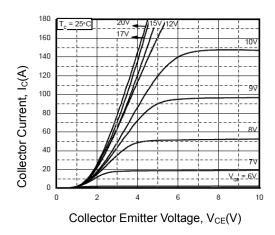


Figure 3. Saturation Voltage vs. Case

Temperature at Variant Current Level

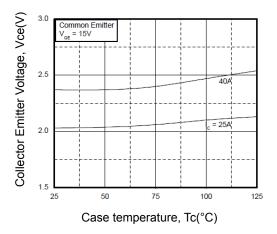


Figure 5. Saturation Voltage vs. V<sub>GE</sub>

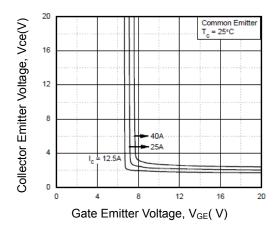


Figure 2. Typical Saturation Voltage Characteristics

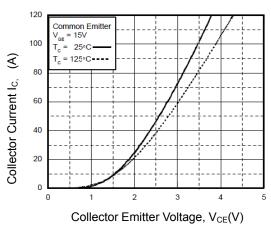


Figure 4. Saturation Voltage vs. V<sub>GE</sub>

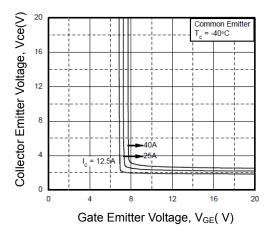
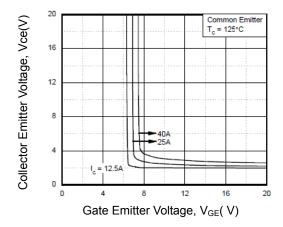


Figure 6. Saturation Voltage vs. V<sub>GE</sub>



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### **Typical Performance Characteristics (Continued)**

Figure 7. Capacitance Characteristics

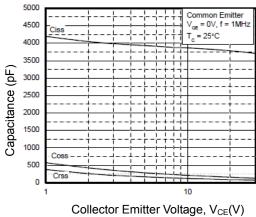


Figure 8. Turn-on Characteristics vs. Gate Resistance

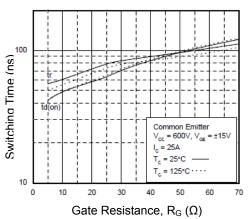


Figure 9. Turn-off Characteristics vs. Gate Resistance

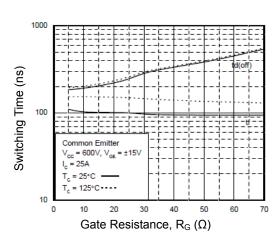


Figure 11. Turn-on Characteristics vs. Collector Current

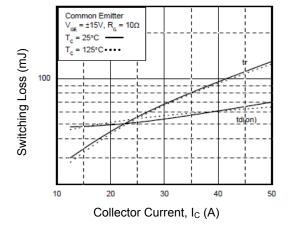


Figure 10. Switching Loss vs. Gate Resistance

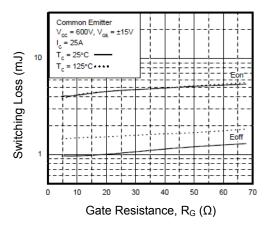
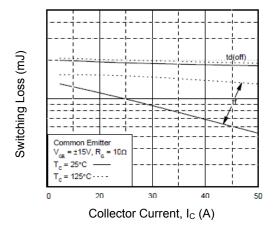


Figure 12. Turn-Off Characteristics vs. **Collector Current** 



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### **Typical Performance Characteristics (Continued)**

Figure 13. Switching Loss vs. Collector Current

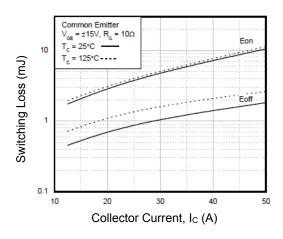


Figure 14. Gate Charge Characteristics

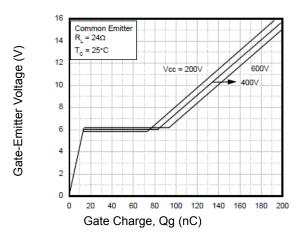


Figure 15. SOA Characteristics

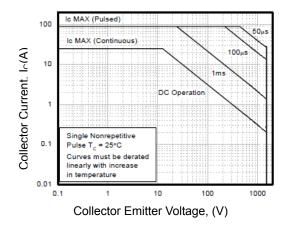


Figure 16. Turn-Off SOA

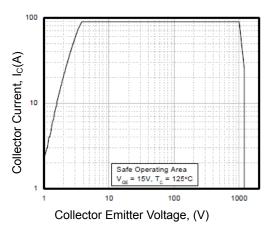
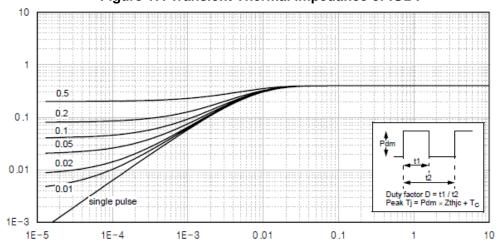


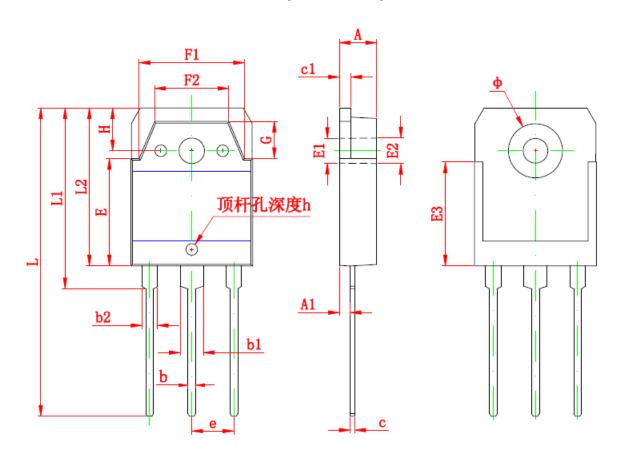
Figure 17. Transient Thermal Impedance of IGBT





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## **TO-3P Mechanical Dimensions (continued)**



| Symbol | Dimensions          | In Millimeters | Dimension | ns In Inches |
|--------|---------------------|----------------|-----------|--------------|
|        | Min                 | Max            | Min       | Max          |
| А      | 4.600               | 5.000          | 0.181     | 0.197        |
| A 1    | 1.200               | 1.600          | 0.047     | 0.063        |
| b      | 0.800               | 1.200          | 0.031     | 0.047        |
| b1     | 2.800               | 3.200          | 0.110     | 0.126        |
| b2     | 1.800               | 2.200          | 0.071     | 0.087        |
| С      | 0.500               | 0.700          | 0.020     | 0.028        |
| c 1    | 1.450               | 1.650          | 0.057     | 0.065        |
| D      | 15.450              | 15.850         | 0.606     | 0.622        |
| Е      | 13.700              | 14.100         | 0.539     | 0.555        |
| E 1    | 3.200 REF           |                | 0.126 REF |              |
| E 2    | 3.300 REF           |                | 0.13      | 0 REF        |
| E 3    | 13.450 REF          |                | 0.530 REF |              |
| F 1    | 13.400              | 13.800         | 0.528     | 0.543        |
| F 2    | 9.400               | 9.800          | 0.370     | 0.386        |
| L      | 39.900              | 40.300         | 1.571     | 1.587        |
| L1     | 23.200              | 23.600         | 0.913     | 0.929        |
| L2     | 20.300              | 20.600         | 0.799     | 0.811        |
| Φ      | 6.900               | 7.100          | 0.272     | 0.280        |
| G      | 5.150               | 5.550          | 0.203     | 0.219        |
| е      | 5.450 TYP 0.215 TYP |                | 5 TYP     |              |
| Н      | 5.000               | REF            | 0.19      | 7 REF        |
| h      | 0.000               | 0.300          | 0.000     | 0.012        |



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